

# Citations for Ion : **Te**

<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1973</b>	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. <b>'Range Distributions of Implanted Ions in SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, and Al<sub>2</sub>O<sub>3</sub>'</b> <i>Appl. Phys. Letters, 22, 490-92 (1973)</i> <i>Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -&gt; SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub></i>	1973-Chu
<b>1973</b>	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. <b>'Ranges and Distributions of Ions Implanted into Dielectrics'</b> <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> <i>Comment : R,dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -&gt; Si, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub></i>	1973-Chu 2
<b>1976</b>	Benmalek, M. Thomas, J. P. Mackowski, J. M. <b>'Ion-Bombardment of Amorphous Semiconductors and Related Evolution of Structural and Electrical Properties'</b> <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 637-647 (1976)</i> <i>Comment : R. 20-300 keV Ne, Ar, Ge, Cd, Te, Xe, Au -&gt; Ge</i>	1976-Benm
<b>1976</b>	Harris, T. J. Sealy, B. J. Surridge, R. K. <b>'Effects of Channelling on the Electrical Properties of Donor Implanted GaAs'</b> <i>Elec. Letters, 12, 664-665 (1976)</i> <i>Comment : R. 90 keV Sn, 90-300 keV Te -&gt; GaAs</i>	1976-Harr
<b>1976</b>	Schmidt, K. -H. Wohlfarth, H. Clerc, H. -G. Lang, W. Schrader, H. <b>'Energy Loss, Energy Straggling and Angular Straggling of Heavy Ions in Carbon Foils'</b> <i>Nucl. Inst. Methods, 134, 157-66 (1976)</i> <i>Comment : S, dS. 80-100 MeV Kr, Rb, Sr, Y, Zr, Nb, Sb, Te -&gt; C</i>	1976-Schm
<b>1977</b>	Surridge, R. K. Sealy, B. J. <b>'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs'</b> <i>Appl. Phys., 10, 911-917 (1977)</i> <i>Comment : R. 200 And 300 keV Sn, Ge, Se, Te -&gt; GaAs</i>	1977-Surr
<b>1977</b>	Surridge, R. K. Sealy, B. J. <b>'Active Layers for Device Applications by using High-Energy Selenium Implantation into GaAs'</b> <i>Elec. Letters, 13, 233-234 (1977)</i> <i>Comment : R. 150 keV Sn, 1 MeV Se -&gt; GaAs</i>	1977-Surr3
<b>1978</b>	Golovchenko, J. A. Venkatesan, T. N. C. <b>'Annealing of Te-Implanted GaAs by Ruby Laser Irradiation'</b> <i>Appl. Phys. Letters, 32, 147-149 (1978)</i> <i>Comment : R. 50 keV Te -&gt; GaAs</i>	1978-Golo

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<b>1979</b>	Santry, D. C. Werner, R. D. Westcott, O. M. <b>'The Range of 120 keV Ions in Solids'</b> <i>IEEE Trans. Nucl. Sci., Ns-26, 1331-1334 (1979)</i> <i>Comment : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -&gt; Be, C, Al, Si</i>	<b>1979-Sant</b>
<b>1986</b>	Geyer, E. Reschke, D. Freitag, K. <b>'Z1 Stopping Power Oscillation in the Nuclear Stopping Regime as Obtained by Time-of-Flight Spectroscopy of Heavy Ions in Hydrogen'</b> <i>Nucl. Inst. Methods, B15, 81-85 (1986)</i> <i>Comment : S. Heavy Ions (49-65) at 26 - 90 keV -&gt; H2 (gas)</i>	<b>1986-Geye</b>
<b>1987</b>	Freitag, K. Reschke, D. Geyer, E. <b>'Stopping Power Measurements for Low Energy Ions in Gases by Time-of-Flight Spectroscopy'</b> <i>Nucl. Inst. Methods, B27, 344-352 (1987)</i> <i>Comment : S. Heavy Ions (49-65) at 27 - 90 keV -&gt; H2 (gas)</i>	<b>1987-Frei</b>
<b>2000</b>	Bimbot, R. Khoumri, A. Fahli, A. Barbey, S. Benfoughal, T. <b>'Stopping Powers of Gases for 40 MeV/u Tellurium Ions'</b> <i>Nucl. Inst. Methods, B170, 329-335 (2000)</i> <i>Comment : S. Te -&gt; H, He, N, Ne, Kr</i>	<b>2000-Bimb</b>